2N3055AG (NPN), MJ15015G (NPN), **MJ15016G (PNP)**

Complementary Silicon High-Power Transistors

These PowerBase complementary transistors are designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055.

Features

- High Current-Gain Bandwidth
- Safe Operating Area
- These Devices are Pb-Free and are RoHS Compliant*

WAAIWUW RATINGS (Note 1)					
Rating	Symbol	Value	Unit		
Collector–Emitter Voltage 2N3055AG MJ15015G, MJ15016G	V _{CEO}	60 120	Vdc		
Collector–Base Voltage 2N3055AG MJ15015G, MJ15016G	V _{CBO}	100 200	Vdc		
Collector–Emitter Voltage Base Reversed Biased 2N3055AG MJ15015G, MJ15016G	V _{CEV}	100 200	Vdc		
Emitter–Base Voltage	V _{EBO}	7.0	Vdc		
Collector Current – Continuous	Ι _C	15	Adc		
Base Current	Ι _Β	7.0	Adc		
Total Device Dissipation (a) $T_C = 25^{\circ}C$ 2N3055AG MJ15015G, MJ15016G Derate above 25^C 2N3055AG MJ15015G, MJ15016G	P _D	115 180 0.65 1.03	W W W/°C W/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C		

MAXIMUM RATINGS (Note 1)

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data. (2N3055A)

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Max	Unit
Thermal Resistance, Junction-to-Case	R_{\thetaJC}	1.52	0.98	°C/W

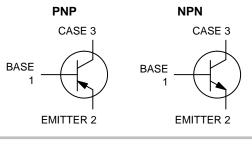
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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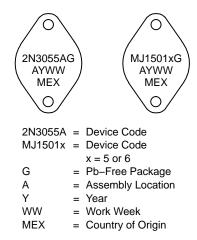
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15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60, 120 VOLTS - 115, 180 WATTS





MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note 2)					•
Collector–Emitter Sustaining Voltage (Note 3) $(I_{C} = 200 \text{ mAdc}, I_{B} = 0)$	2N3055AG MJ15015G, MJ15016G	V _{CEO(sus)}	60 120		Vdc
	2N3055AG MJ15015G, MJ15016G	I _{CEO}	-	0.7 0.1	mAdc
Collector Cutoff Current (Note 3) (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{CEV}	-	5.0 1.0	mAdc
Collector Cutoff Current (V_{CEV} = Rated Value, $V_{BE(off)}$ = 1.5 Vdc, T_{C} = 150°C)	2N3055AG MJ15015G, MJ15016G	I _{CEV}		30 6.0	mAdc
Emitter Cutoff Current (V _{EB} = 7.0 Vdc, I _C = 0)			- -	5.0 0.2	mAdc
SECOND BREAKDOWN (Note 3)					
Second Breakdown Collector Current with Base Forward Biased (t = 0.5 s non-repetitive) 2N3055AG (V _{CE} = 60 Vdc) MJ15015G, MJ15016G		I _{S/b}	1.95 3.0		Adc
ON CHARACTERISTICS (Note 2 and 3)					•
$ DC Current Gain \\ (I_C = 4.0 \ Adc, \ V_{CE} = 2.0 \ Vdc) \\ (I_C = 4.0 \ Adc, \ V_{CE} = 4.0 \ Vdc) \\ (I_C = 10 \ Adc, \ V_{CE} = 4.0 \ Vdc) $		h _{FE}	10 20 5.0	70 70 -	-
Collector–Emitter Saturation Voltage ($I_C = 4.0 \text{ Adc}, I_B = 400 \text{ mAdc}$) ($I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc}$) ($I_C = 15 \text{ Adc}, I_B = 7.0 \text{ Adc}$)		V _{CE(sat)}	- - -	1.1 3.0 5.0	Vdc
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	0.7	1.8	Vdc
DYNAMIC CHARACTERISTICS (Note 3)					
Current–Gain – Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 MHz)	2N3055AG, MJ15015G MJ15016G	f _T	0.8 2.2	6.0 18	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)		C _{ob}	60	600	pF
SWITCHING CHARACTERISTICS (2N3055AG or	nly) (Note 3)			•	•
RESISTIVE LOAD					
Delay Time		t _d	_	0.5	μs
Rise Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 4.0 \text{ Adc},$	t _r	_	4.0	μs
Storage Time	$I_{B1} = I_{B2} = 0.4 \text{ Adc},$ $t_p = 25 \ \mu s \ \text{Duty Cycle} \le 2\%$	t _s	_	3.0	μs
Fall Time		t _f	_	6.0	μs

Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤
 Indicates JEDEC Registered Data. (2N3055A)

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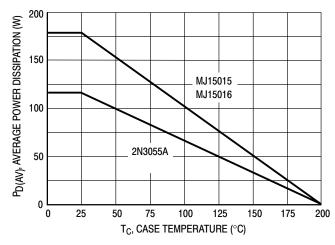
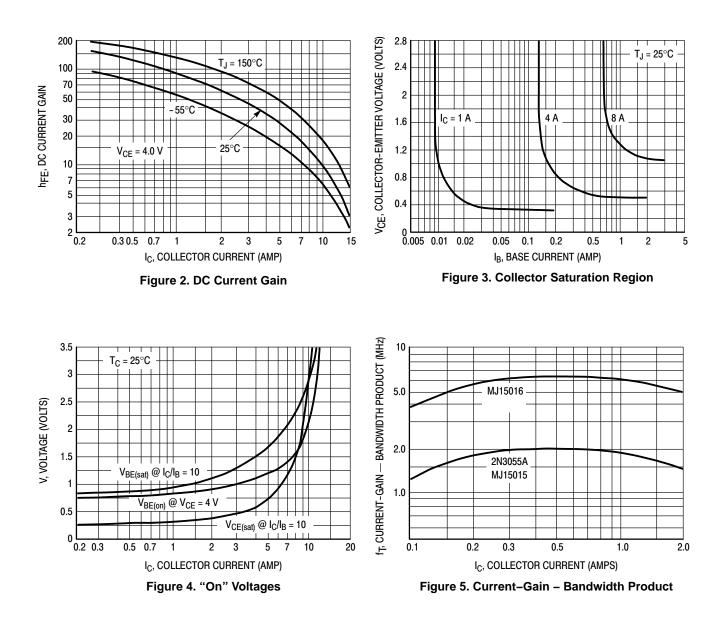


Figure 1. Power Derating



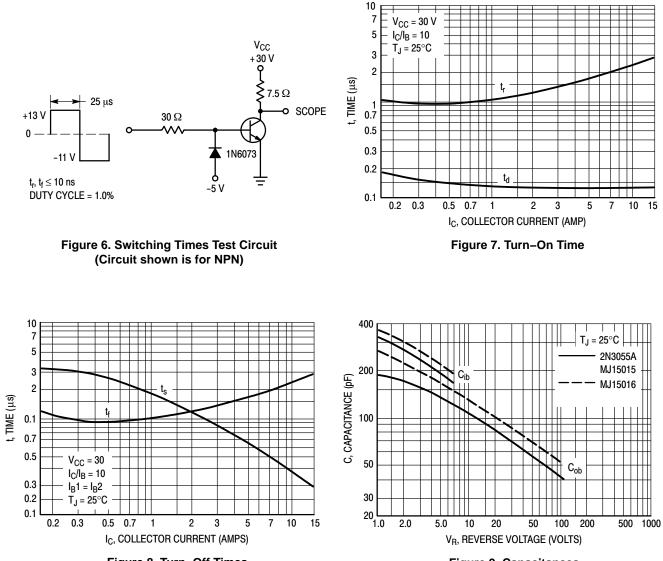
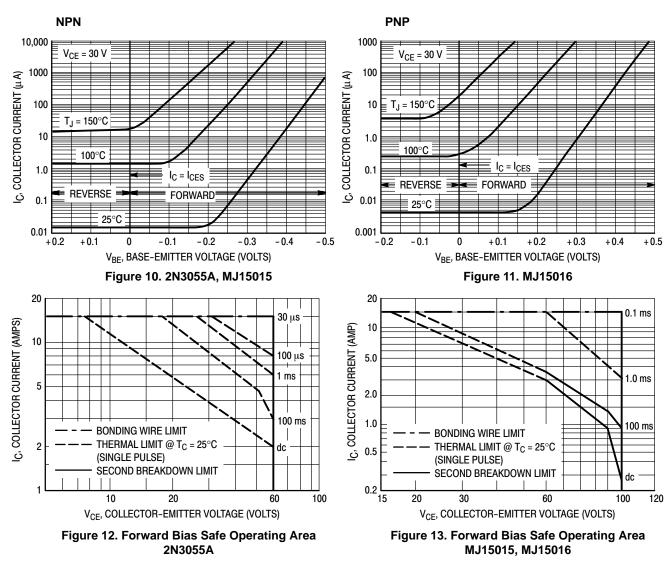


Figure 8. Turn–Off Times

Figure 9. Capacitances

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COLLECTOR CUT-OFF REGION



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 12 and 13 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

ORDERING INFORMATION

Device	Package	Shipping
2N3055AG	TO-204 (Pb-Free)	100 Units / Tray
MJ15015G	TO-204 (Pb-Free)	100 Units / Tray
MJ15016G	TO-204 (Pb-Free)	100 Units / Tray

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



DIMENSIONS			
SCALE 1:1	TO–204 (TO–3) CASE 1–07 ISSUE Z)	DATE 05/18/1988
$ \begin{array}{c} $	$ \begin{array}{c} $	NOTES: 1. DIMENSIONING AND TC Y14.5M, 1982. 2. CONTROLLING DIMENS 3. ALL RULES AND NOTES REFERENCED TO-204A MIN MAX A 1.550 REF B 1.050 C 0.250 0.335 D 0.038 0.043 E 0.055 0.070 G 0.430 BSC H 0.215 BSC K 0.440 0.480 L 0.665 BSC N 0.830 Q 0.151 0.165 U 1.187 BSC V 0.131 0.188	ION: INCH.
STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR STYLE 6: PIN 1. GATE 2. EMITTER CASE: COLLECTOR	STYLE 2: STYLE 3: PIN 1. BASE PIN 1. GATE 2. COLLECTOR 2. SOURCE CASE: EMITTER CASE: DRAIN STYLE 7: STYLE 8: PIN 1. ANODE PIN 1. CATHODE #1 2. OPEN 2. CATHODE #2 CASE: CATHODE CASE: ANODE	STYLE 4: STYLE 5: PIN 1. GROUND 2. INPUT CASE: OUTPUT STYLE 9: PIN 1. ANODE #1 2. ANODE #2 CASE: CATHODE	E AL TRIP/DELAY

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